

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ.)
40	0.0050 at V _{GS} = 10 V	70	67 nC
	0.0060 at V _{GS} = 4.5 V	65	

FEATURES

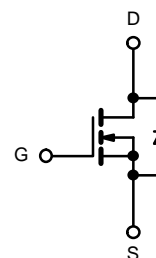
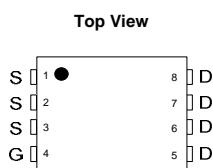
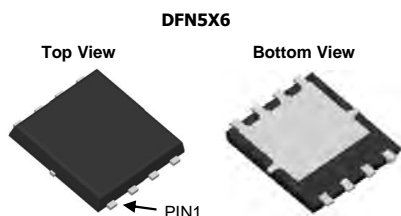
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested



RoHS
COMPLIANT

APPLICATIONS

- Notebook PC Core
- VRM/POL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	40	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C)	I _D	T _C = 25 °C	70 ^{a, e}	A
		T _C = 70 °C	60 ^e	
		T _A = 25 °C	19 ^{b, c}	
		T _A = 70 °C	18.6 ^{b, c}	
Pulsed Drain Current	I _{DM}	120		
Avalanche Current Pulse	L = 0.1 mH	I _{AS}	21	mJ
Single Pulse Avalanche Energy		E _{AS}	47.2	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	70 ^{a, e}	A
		T _A = 25 °C	2.36 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	100 ^a	W
		T _C = 70 °C	55	
		T _A = 25 °C	6.15 ^{b, c}	
		T _A = 70 °C	3.07 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	47	56	°C/W
Maximum Junction-to-Case	Steady State	R _{thJC}	0.8	1.1	

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under steady state conditions is 90 °C/W.
- e. Calculated based on maximum junction temperature. Package limitation current is 80 A.

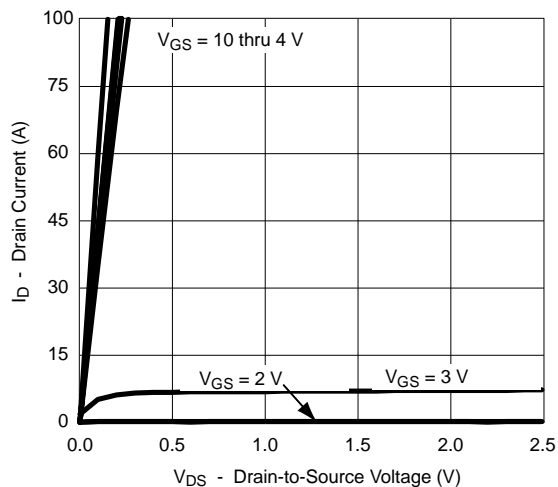
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		35		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			1	μA
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	70			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 32 A		0.005		Ω
		V _{GS} = 4.5 V, I _D = 29 A		0.006		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 32 A		110		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = 12.5 V, V _{GS} = 0 V, f = 1 MHz		1195		pF
Output Capacitance	C _{oss}			975		
Reverse Transfer Capacitance	C _{rss}			670		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 32 A		67		nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 29 A		57.3		
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 29 A		31		nC
Gate-Drain Charge	Q _{gd}			25		
Gate Resistance	R _g		f = 1 MHz		1.4	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.555 Ω I _D ≅ 27 A, V _{GEN} = 10 V, R _g = 1 Ω		18	27	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.625 Ω I _D ≅ 24 A, V _{GEN} = 4.5 V, R _g = 1 Ω		55	83	
Rise Time	t _r			180	270	
Turn-Off Delay Time	t _{d(off)}			55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			70	A
Pulse Diode Forward Current ^a	I _{SM}				100	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a			27		ns
Reverse Recovery Rise Time	t _b			25		

Notes:

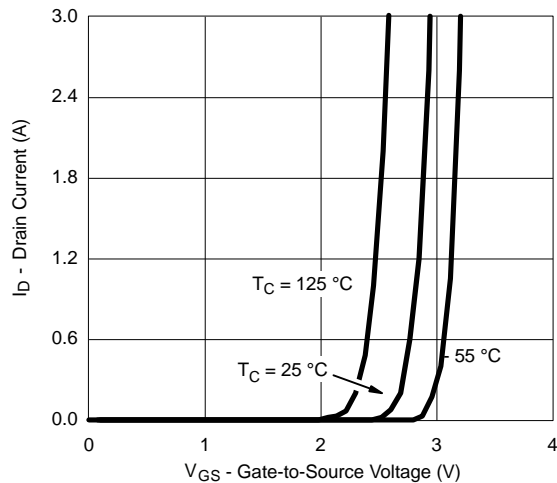
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

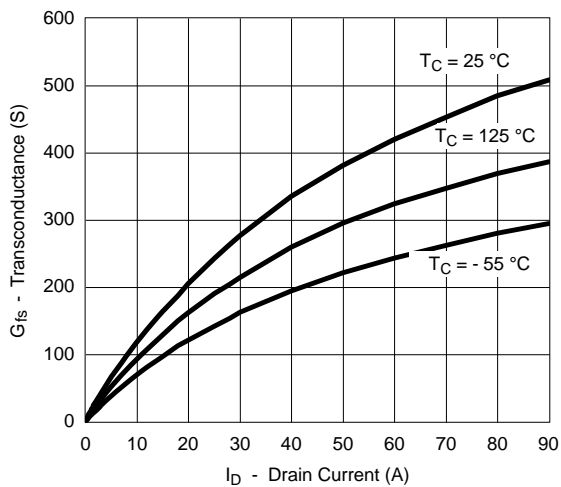
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



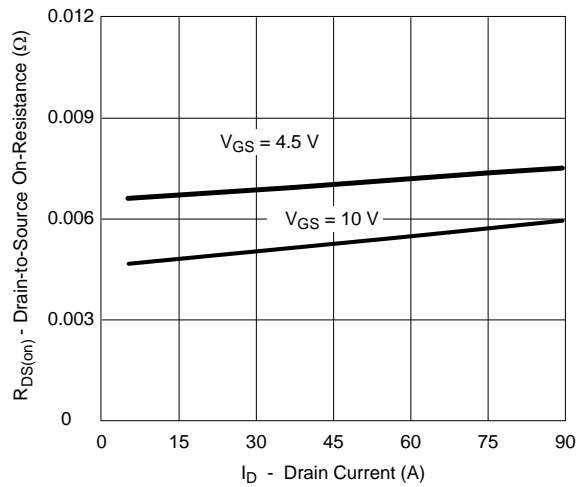
Output Characteristics



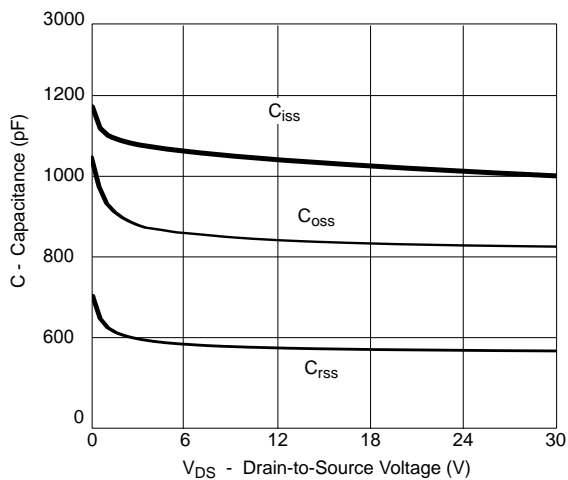
Transfer Characteristics



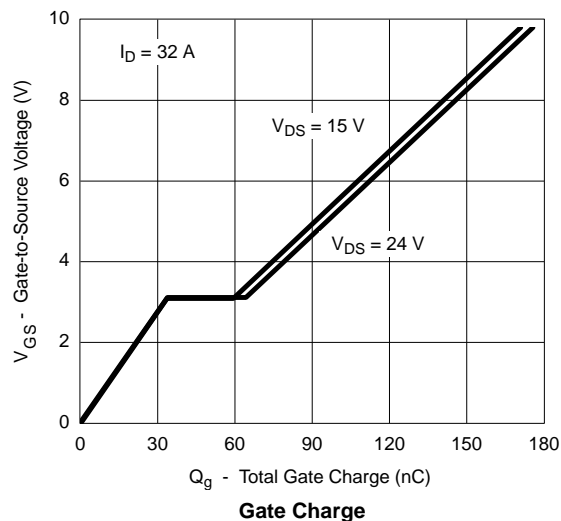
Transconductance



$R_{DS(on)}$ vs. Drain Current

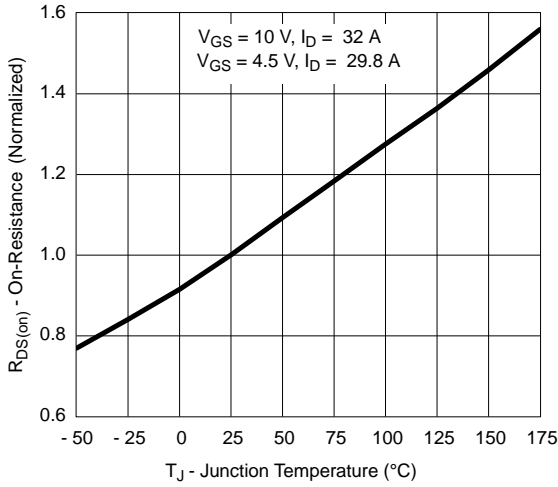


Capacitance

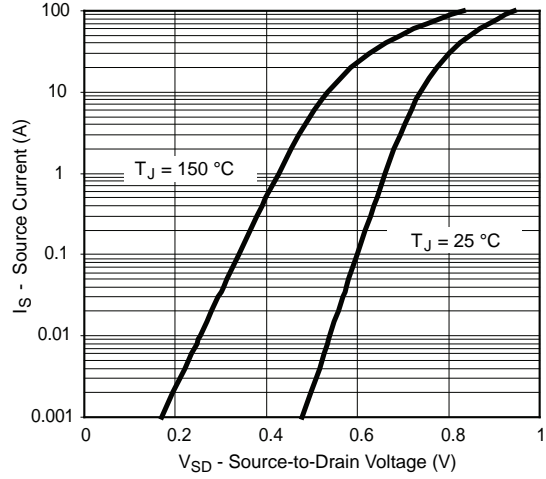


Gate Charge

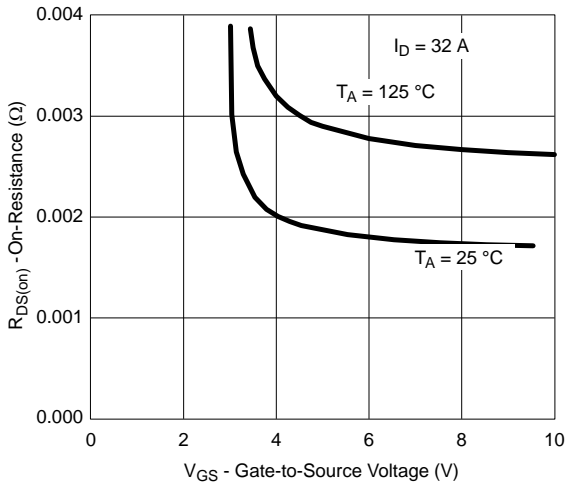
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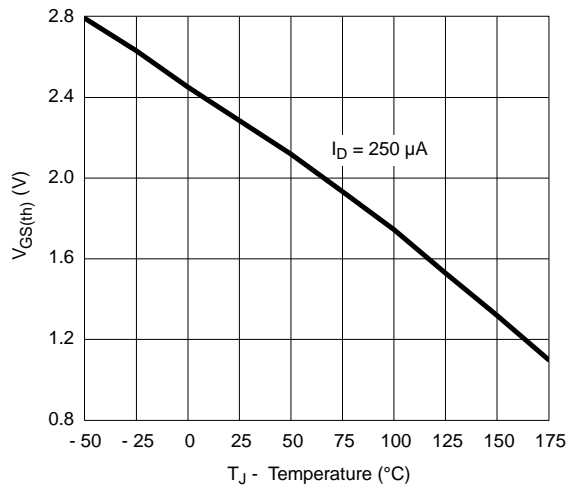
On-Resistance vs. Junction Temperature



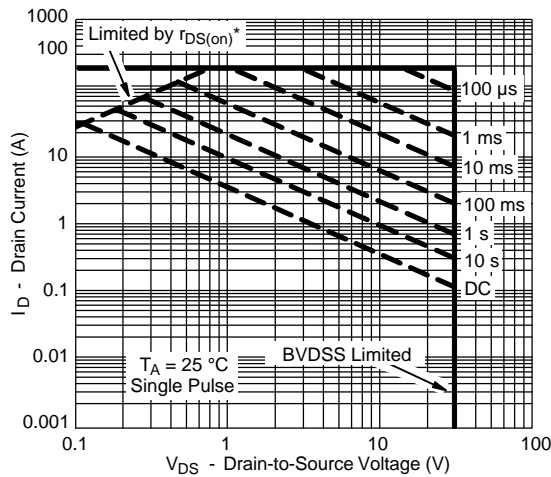
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

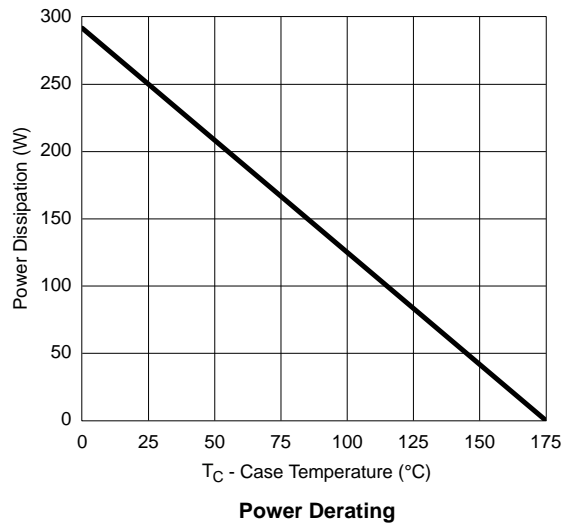
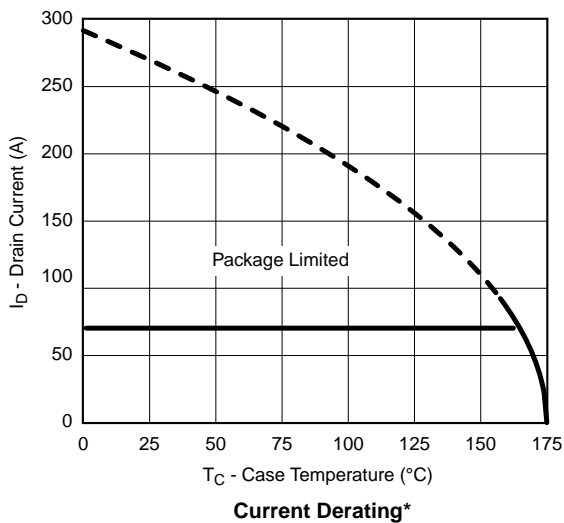


Threshold Voltage

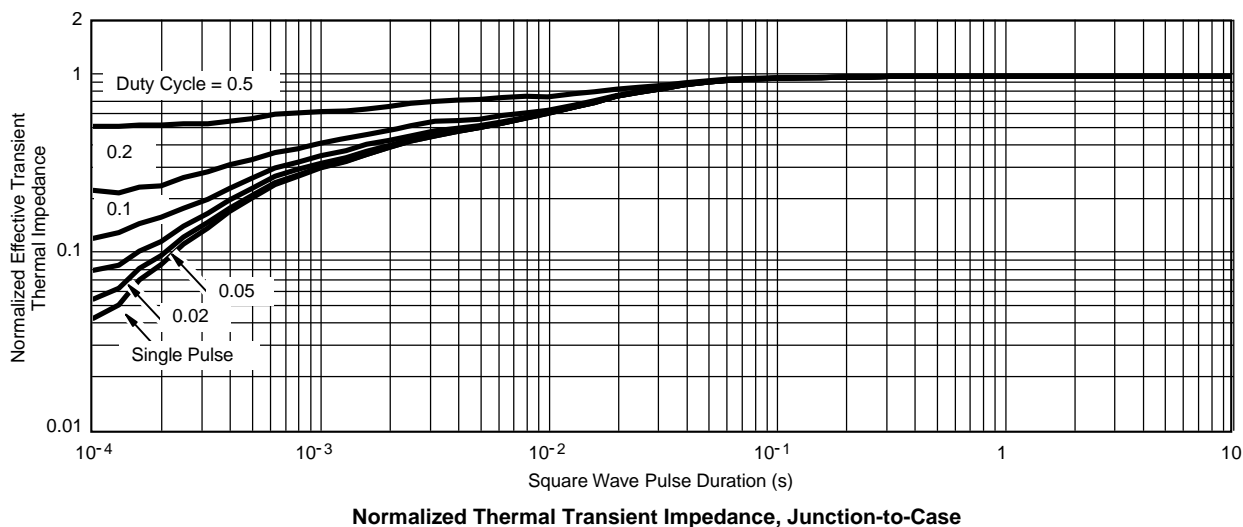


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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